

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6130453").PN.	USPAT	OR	OFF	2005/04/06 11:27
L2	1	1 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:37
L3	1	"5680345".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:34
L4	1	"5656544".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:34
L5	1	"5640031".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:34
L6	1	"5512505".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:35
L7	1	"5495441".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:35
L8	1	"5492846".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:35
L9	1	"5479368".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:35
L10	1	"5386132".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:36
L11	1	"4929988".PN.	USPAT; USOCR	OR	ON	2005/04/06 11:36
L12	1	3 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:39

L13	1	4 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:40
L14	1	5 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:54
L15	1	6 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:42
L16	1	7 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:43

L17	1	8 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:44
L18	1	9 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:46
L19	1	10 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:47
L20	0	(patterned adj mask) and floating and contol and gate and trench and etching and source and drain and spacer and cvd and polysilicon	USPAT	OR	ON	2005/04/06 11:50
L21	0	mask and floating and contol and gate and trench and etching and source and drain and spacer and cvd and polysilicon and pair	USPAT	OR	ON	2005/04/06 11:49
L22	17	(patterned adj mask) and floating and control and gate and trench and etching and source and drain and spacer and cvd and polysilicon	USPAT	OR	ON	2005/04/06 11:53
L23	1	("6214667").PN.	USPAT	OR	OFF	2005/04/06 11:54
L24	1	("6153471").PN.	USPAT	OR	OFF	2005/04/06 11:54

L25	1	23 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:58
L26	1	24 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing)	USPAT	OR	ON	2005/04/06 11:58
L27	2470	438/257	USPAT	OR	ON	2005/04/06 11:59
L28	2179	438/238	USPAT	OR	ON	2005/04/06 12:00
L29	552	438/263	USPAT	OR	ON	2005/04/06 12:00
L30	1314	438/264	USPAT	OR	ON	2005/04/06 12:00
L31	1200	438/381	USPAT	OR	ON	2005/04/06 12:00
L32	538	438/267	USPAT	OR	ON	2005/04/06 12:00
L33	1122	438/680	USPAT	OR	ON	2005/04/06 12:00
L34	1453	438/700	USPAT	OR	ON	2005/04/06 12:00
L35	832	438/712	USPAT	OR	ON	2005/04/06 12:00
L36	204	438/718	USPAT	OR	ON	2005/04/06 12:00
L37	852	438/719	USPAT	OR	ON	2005/04/06 12:00
L38	3376	438/692	USPAT	OR	ON	2005/04/06 12:01
L39	884	438/720	USPAT	OR	ON	2005/04/06 12:01
L40	748	438/734	USPAT	OR	ON	2005/04/06 12:01
L41	451	438/735	USPAT	OR	ON	2005/04/06 12:01
L42	744	438/770	USPAT	OR	ON	2005/04/06 12:01